## IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re the Application of		•		
Pendharkar	(TI-34637)			
Serial No/,		Group Art Unit:		
Filed: Herewith		Examiner:		
For: Drain Extended MOS Transistor with Improved Breakdown Robustness				

## **INFORMATION DISCLOSURE STATEMENT**

Commissioner for Patents P.O. Box 1450 Alexandria, VA 22313-1450

Dear Sir:

Applicant brings the reference listed on the enclosed PTO/SB/08A to the attention of the Patent and Trademark Office relative to this application.

A copy of the reference is enclosed. The reference is in the English language. As such, no additional statement of relevance is provided in this paper.

Consideration of this information in the prosecution of this application is respectfully requested.

Respectfully submitted,

Rodney M. Anderson Registry No. 31,939 Attorney for Applicant

Anderson, Levine & Lintel, L.L.P. 14785 Preston Road, Suite 650 Dallas, Texas 75254 (972) 664-9554

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PTO/SB/08B (08-03)

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INFORMATION DISCLOSURE		Herewith	
STATEMENT BY APPLICANT	First Named Inventor	Pendharkar	
(Use as many sheets as necessary)	Art Unit		
(eee 20 many sheets as necessary)	Examiner Name		
Sheet 1 of 1	Attorney Docket Number	TI-34637	

NON PATENT LITERATURE DOCUMENTS  Examiner   Cite   Include name of the author (in CAPITAL LETTERS) title of the acticle (in th						
Initials*	No.1	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.				
		Aur and Chatterjee, "Robustness of LDD nMOS Transistors Subjected to Measurement of Drain Breakdown Voltage", Extended Abstracts of the 22nd Conference on Solid State Devices and Materials, Paper C-6-8 (1990), pp. 319-22.				
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Examiner	 Date	
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	 Considered	

<sup>\*</sup>EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

<sup>1</sup> Applicant's unique citation designation number (optional). 2 Applicant is to place a check mark here if English language Translation is attached.

This collection of information is required by 37 CFR 1.98. The information is required to obtain or retain a benefit by the public which is to file (and by the USPTO to process) an application. Confidentiality is governed by 35 U.S.C. 122 and 37 CFR 1.14. This collection is estimated to take 2 hours to complete, including gathering, preparing, and submitting the completed application form to the USPTO. Time will vary depending upon the individual case. Any comments on the amount of time you require to complete this form and/or suggestions for reducing this burden, should be sent to the Chief Information Officer, U.S. Patent and Trademark Office, P.O. Box 1450, Alexandria, VA 22313-1450. DO NOT SEND FEES OR COMPLETED FORMS TO THIS ADDRESS. SEND TO: Commissi ner for Patents, P.O. Box 1450, Alexandria, VA 22313-1450.